

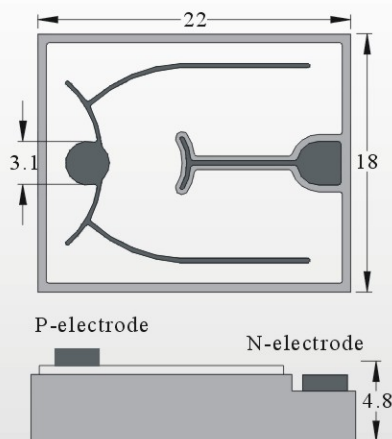


LatticePower

Product Introduction



LPABG22A



LPABG22A

Mechanical Specifications

Size:
 Chip Size: 18mil x 22mil
 (460±25µm x 560±25µm)
 Chip Thickness: 4.8mil(120±10µm)
 Pad Size: 3.1mil(78±10µm)

Pad Metal
 P Electrode: Au
 N Electrode: Au

Unit: mil

Typical Electrical/Optical Characteristics:

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _f	I _f =60mA	2.8	---	3.6	V
Reverse Current	I _r	V _r =5V	---	---	1	µA
Dominant Wavelength	λ _d	I _f =60mA	445	---	475	nm
Spectra Half-width	Δλ	I _f =60mA	---	---	30	nm
Luminous Intensity	P _o	I _f =60mA	70	---	100	mW

Parameters range:

Wd(nm) Po(mW)	447.5-450	450-452.5	452.5-455	455-457.5	457.5-460	460-462.5
95-100	FBHV	GAHV	GBHV	HAHV	HBHV	IAHV
90-95	FBGV	GAGV	GBGV	HAGV	HBGV	IAGV
85-90	FBFV	GAFV	GBFV	HAFV	HBFV	IAFV
80-85	FBEV	GAEV	GBEV	HAEV	HBEV	IAEV
75-80	FBDV	GADV	GBDV	HADV	HBDV	IADV
70-75	FBCV	GACV	GBCV	HACV	HBCV	IACV

Notes:

- The Electrical/Optical Characteristics are measured with LatticePower electro-optical equipment at (T_a=25°C) without an encapsulant.
- GaNLED chip is an electrostatic sensitive product, so ESD protection during chip handling is recommended.
- We welcome customer's enquiry for special requirements.

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